

PUMD9

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

1 July 2022

Product data sheet

1. General description

NPN/PNP Resistor-Equipped double Transistor (RET) in a very small SOT363 (SC-88) Surface-Mounted Device (SMD) plastic package.

NPN/NPN complement: PUMH9 PNP/PNP complement: PUMB9

2. Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- · Reduces component count
- Reduces pick and place costs

3. Applications

- Digital application in automotive and industrial segments
- · Cost-saving alternative for BC847/BC857 series in digital applications
- · Controlling IC inputs
- Switching loads

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Per transistor,	Per transistor, for the PNP transistor with negative polarity							
V _{CEO}	collector-emitter voltage	open base		-	-	50	V	
I _O	output current			-	-	100	mA	
R1	bias resistor 1 (input)		[1]	7	10	13	kΩ	
R2/R1	bias resistor ratio		[1]	3.7	4.7	5.7		

[1] See "Section 11: Test information" for resistor calculation and test conditions.



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	GND1	GND (emitter) TR1		O1 I2 GND2
2	I1	input (base) TR1		
3	O2	output (collector) TR2	6 5 4	R1 R2
4	GND2	GND (emitter) TR2		TR2
5	12	input (base) TR2		TR1 R2 R1
6	O1	output (collector) TR1	☐1 ☐2 ☐3 TSSOP6 (SOT363)	
				GND1 I1 O2 006aaa143

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PUMD9		plastic, surface-mounted package; 6 leads; 0.65 mm pitch; 2.1 mm x 1.25 mm x 0.95 mm body	SOT363			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PUMD9	D%9

[1] % = placeholder for manufacturing site code

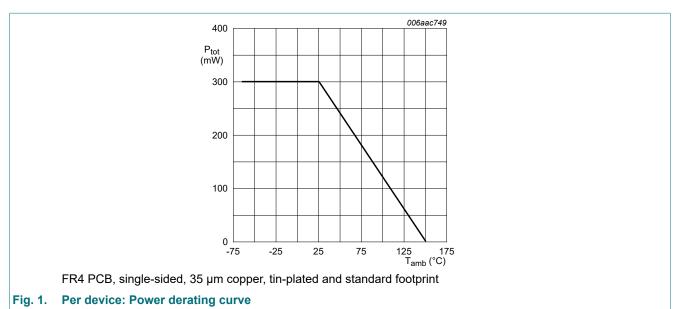
8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
Per transiste	or, for the PNP transistor wit	n negative polarity			'	
V _{CBO}	collector-base voltage	open emitter		-	50	V
V _{CEO}	collector-emitter voltage	open base		-	50	V
V _{EBO}	emitter-base voltage	open collector		-	6	V
V _I	input voltage	input voltage TR1		-	40	V
				-	-6	V
		input voltage TR2		-	6	V
				-	-40	V
lo	output current			-	100	mA
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	200	mW
Per device			1		'	
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	300	mW
T _j	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided, 35 µm copper, tin-plated and standard footprint.



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Per transistor	Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	625	K/W
Per device	Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air	[1]	-	-	417	K/W

[1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.

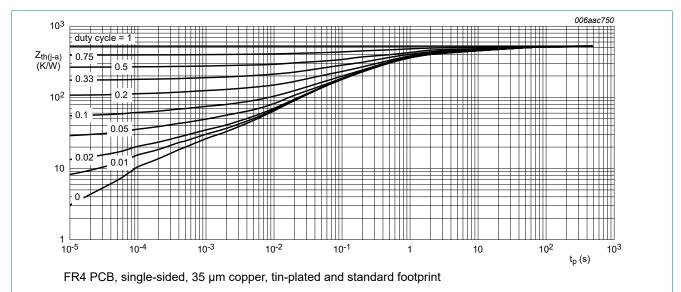


Fig. 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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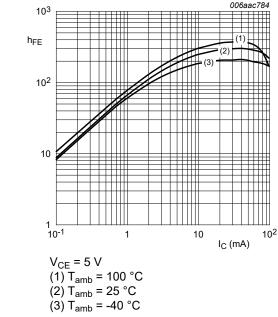
10. Characteristics

Table 7. Characteristics

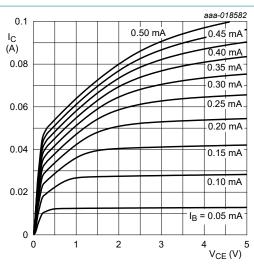
r, for the PNP transistor v	vith negative polarity		_			
11 (1						
collector-base breakdown voltage	$I_C = 100 \ \mu A; I_E = 0 \ A; T_{amb} = 25 \ ^{\circ}C$		50	-	-	V
collector-emitter breakdown voltage	_C = 2 mA; I _B = 0 A; T _{amb} = 25 °C		50	-	-	V
collector-base cut-off current	V _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C	' _{CB} = 50 V; I _E = 0 A; T _{amb} = 25 °C		-	100	nA
collector-emitter cut-off	V _{CE} = 30 V; I _B = 0 A; T _{amb} = 25 °C		-	-	100	nA
current	V _{CE} = 30 V; I _B = 0 A; T _j = 150 °C		-	-	5	μA
emitter-base cut-off current	$V_{EB} = 5 \text{ V}; I_{C} = 0 \text{ mA}; T_{amb} = 25 \text{ °C}$		-	-	150	μΑ
DC current gain	$V_{CE} = 5 \text{ V}; I_{C} = 5 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		100	-	-	
collector-emitter saturation voltage	$I_C = 5 \text{ mA}; I_B = 0.25 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		-	-	100	mV
off-state input voltage	V _{CE} = 5 V; I _C = 100 μA; T _{amb} = 25 °C		-	0.7	0.5	V
on-state input voltage	$V_{CE} = 0.3 \text{ V}; I_{C} = 1 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$		1.4	0.8	-	V
bias resistor 1 (input)		[1]	7	10	13	kΩ
bias resistor ratio		[1]	3.7	4.7	5.7	
collector capacitance	$V_{CB} = 10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A}; f = 1 \text{ MHz}; $ $T_{amb} = 25 \text{ °C}$		-	-	2.5	pF
transition frequency	$V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA}; f = 100 \text{ MHz};$ $T_{amb} = 25 \text{ °C}$	[2]	-	230	-	MHz
collector capacitance	$V_{CB} = -10 \text{ V}; I_E = 0 \text{ A}; i_e = 0 \text{ A};$ f = 1 MHz; $T_{amb} = 25 \text{ °C}$		-	-	3	pF
transition frequency	V_{CE} = -5 V; I_{C} = -10 mA; f = 100 MHz; T_{amb} = 25 °C	[2]	-	180	-	MHz
	collector-emitter breakdown voltage collector-base cut-off current collector-emitter cut-off current emitter-base cut-off current DC current gain collector-emitter saturation voltage off-state input voltage bias resistor 1 (input) bias resistor ratio collector capacitance transition frequency	collector-emitter breakdown voltage	collector-emitter breakdown voltage	$ \begin{array}{c} \text{collector-emitter} \\ \text{breakdown voltage} \\ \\ \text{collector-base cut-off} \\ \text{current} \\ \\ \text{collector-emitter cut-off} \\ \text{current} \\ \\ \text{collector-emitter cut-off} \\ \text{current} \\ \\ \text{V}_{CE} = 30 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \\ \text{current} \\ \\ \text{V}_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \\ \text{current} \\ \\ \text{V}_{CE} = 30 \text{ V}; \text{ I}_{B} = 0 \text{ A}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \\ \text{current} \\ \\ \text{DC current gain} \\ \text{V}_{CE} = 5 \text{ V}; \text{ I}_{C} = 0 \text{ mA}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \\ \text{collector-emitter} \\ \text{saturation voltage} \\ \text{off-state input voltage} \\ \text{off-state input voltage} \\ \text{V}_{CE} = 5 \text{ V}; \text{ I}_{C} = 100 \mu\text{A}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \\ \text{on-state input voltage} \\ \text{V}_{CE} = 0.3 \text{ V}; \text{ I}_{E} = 100 \mu\text{A}; \text{ T}_{amb} = 25 ^{\circ}\text{C} \\ \\ \text{on-state input voltage} \\ \text{bias resistor 1 (input)} \\ \text{bias resistor ratio} \\ \\ \text{Collector capacitance} \\ \text{V}_{CB} = 10 \text{ V}; \text{ I}_{E} = 0 \text{ A}; \text{ I}_{e} = 0 \text{ A}; \text{ I}_{e} = 10 \text{ MHz}; \\ \text{T}_{amb} = 25 ^{\circ}\text{C} \\ \\ \text{transition frequency} \\ \text{V}_{CE} = 5 \text{ V}; \text{ I}_{C} = 10 \text{ mA}; \text{ I}_{e} = 0 \text{ A}; \\ \text{I}_{e} = 0 A$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$	$ \begin{array}{c ccccccccccccccccccccccccccccccccccc$

^[1] See "Section 11: Test information" for resistor calculation and test conditions.

^[2] Characteristics of built-in transistor

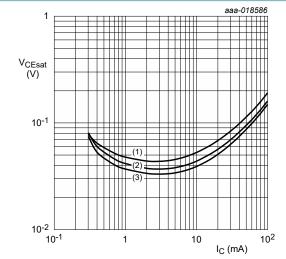


TR1 (NPN): DC current gain as a function of Fig. 3. collector current; typical values



 $T_{amb} = 25 \, ^{\circ}C$

Fig. 4. TR1 (NPN): Collector current as a function of collector-emitter voltage; typical values



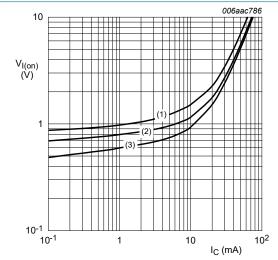
 $I_{\rm C}/I_{\rm B}=20$

(1) $T_{amb} = 100 \, ^{\circ}C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 5. TR1 (NPN): Collector-emitter saturation voltage as a function of collector current; typical values



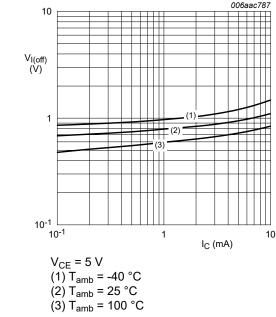
 $V_{CE} = 0.3 V$

(1) $T_{amb} = -40 \, ^{\circ}C$

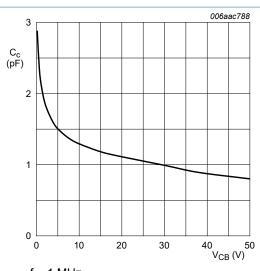
 $(2) T_{amb} = 25 °C$

(3) $T_{amb} = 100 \, ^{\circ}C$

TR1 (NPN): On-state input voltage as a function Fig. 6. of collector current; typical values

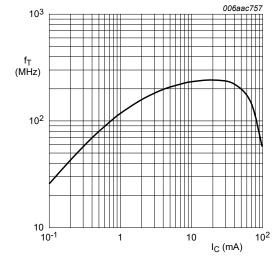


TR1 (NPN): Off-state input voltage as a function Fig. 7. of collector current; typical values



f = 1 MHz T_{amb} = 25 °C

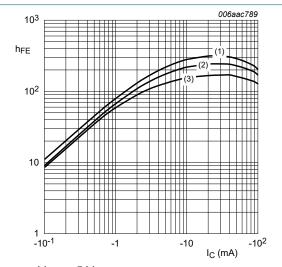
Fig. 8. TR1 (NPN): Collector capacitance as a function of collector-base voltage; typical values



f = 100 MHz $T_{amb} = 25 \, ^{\circ}C$

 $V_{CE} = 5 V$

Fig. 9. TR1 (NPN): Transition frequency as a function of collector current; typical values of built-in transistor



 $V_{CE} = -5 V$

 $(1) T_{amb} = 100 °C$

(2) $T_{amb} = 25 \, ^{\circ}C$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig. 10. TR2 (PNP): DC current gain as a function of collector current; typical values

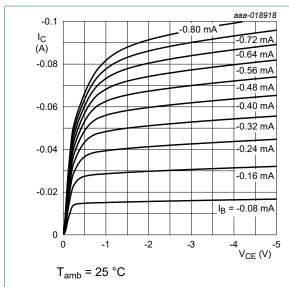
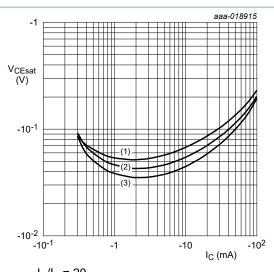
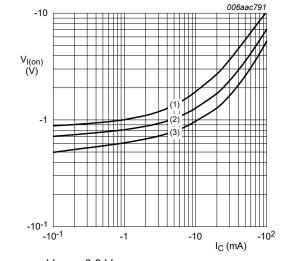


Fig. 11. TR2 (PNP): Collector current as a function of collector-emitter voltage; typical values



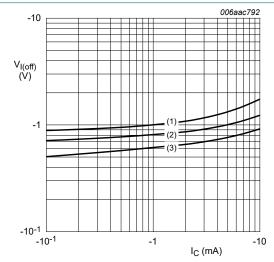
 $I_{\rm C}/I_{\rm B}=20$ (1) T_{amb} = 100 °C (2) T_{amb} = 25 °C (3) T_{amb} = -40 °C

Fig. 12. TR2 (PNP): Collector-emitter saturation voltage as a function of collector current; typical values



 $V_{CE} = -0.3 \text{ V}$ (1) T_{amb} = -40 °C (2) $T_{amb} = 25 \, ^{\circ}C$ (3) T_{amb} = 100 °C

of collector current; typical values



 $V_{CE} = -5 V$ (1) $T_{amb} = -40 \, ^{\circ}C$ (2) $T_{amb} = 25 \, ^{\circ}C$ (3) $T_{amb} = 100 \, ^{\circ}C$

Fig. 13. TR2 (PNP): On-state input voltage as a function | Fig. 14. TR2 (PNP): Off-state input voltage as a function of collector current; typical values

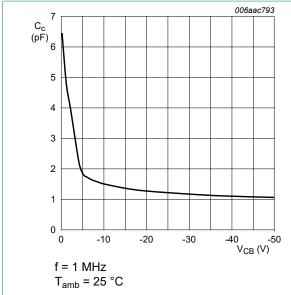


Fig. 15. TR2 (PNP): Collector capacitance as a function of collector-base voltage; typical values

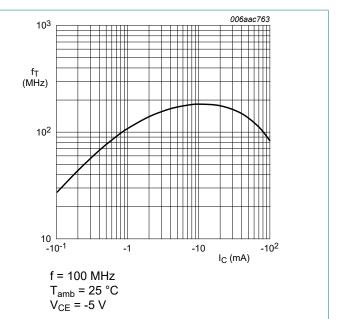


Fig. 16. TR2 (PNP): Transition frequency as a function of collector current; typical values of built-in transistor

11. Test information

Resistor calculation

• Calculation of bias resistor 1 (R1)

$$R1 = \frac{V(I12) - V(I11)}{I12 - I11}$$

· Calculation of bias resistor ratio (R2/R1)

$$\frac{R2}{R1} = \frac{V(I14) - V(I13)}{R1 \cdot (I14 - I13)} - 1$$

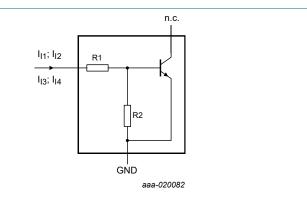


Fig. 17. TR1 (NPN): Resistor test circuit

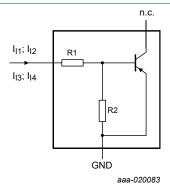


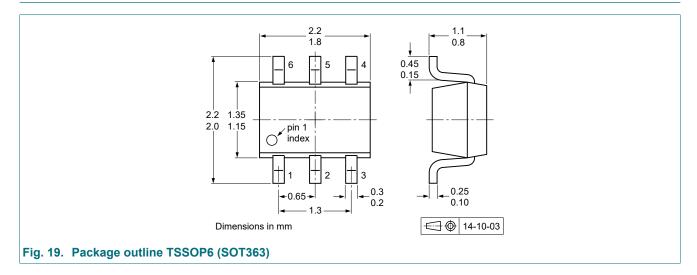
Fig. 18. TR2 (PNP): Resistor test circuit

Resistor test conditions

Table 8. Resistor test conditions

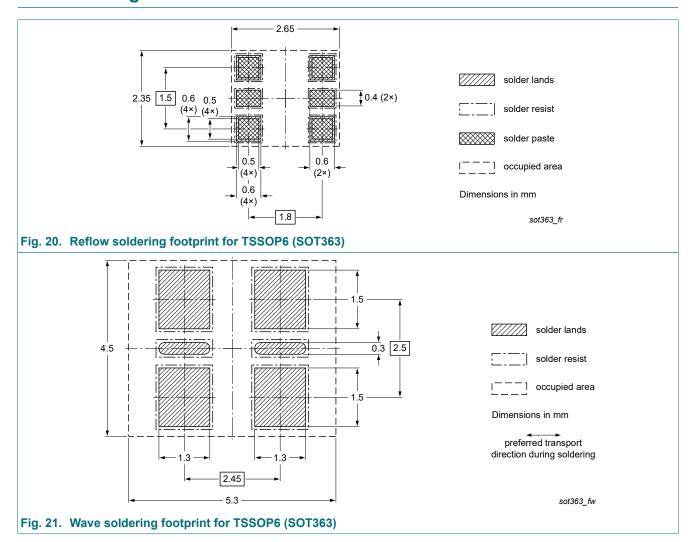
Type number	R1 (kΩ)	R2 (kΩ)	Test conditions					
			I _{I1}	I ₁₂	I ₁₃	I ₁₄		
Per transistor, fo	Per transistor, for the PNP with negative polarity							
PUMD9	10	47	90 μΑ	140 μΑ	-55 μΑ	-105 μA		

12. Package outline



11 / 15

13. Soldering



50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

14. Revision history

Table 9. Revision history

Table 9. Revision history							
Data sheet ID	Release date	Data sheet status	Change notice	Supersedes			
PUMD9 v.7	20220701	Product data sheet	-	PEMD9_PUMD9 v.6			
Modification:	of Nexperia. Legal texts hat Family data so Product chan automotive (-	The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. Family data sheet reduced to single type data sheet. Product changed to non-automotive qualification. Please refer to nexperia.com for automotive (-Q) product alternative(s). Packing information removed.					
PEMD9_PUMD9 v.6	20111122	Product data sheet	-	PEMD9_PUMD9 v.5			
PEMD9_PUMD9 v.5	20040415	Product data sheet	-	PEMD9_PUMD9 v.4			
PEMD9_PUMD9 v.4	20031104	Product specification	-	PEMD9 v.2 PUMD9 v.3			
PEMD9 v.2	20020905	Product specification	-	PEMD9 v.1			
PEMD9 v.1	20011022	Preliminary specification	-	-			
PUMD9 v.3	20010216	Product specification	-	PUMD9 v.2			
PUMD9 v.2	19990520	Product specification	-	PUMD9 v.1			
PUMD9 v.1	19990107	Product specification	-	-			

50 V, 100 mA NPN/PNP resistor-equipped double transistor; R1 = 10 k Ω , R2 = 47 k Ω

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- Please consult the most recently issued document before initiating or completing a design.
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